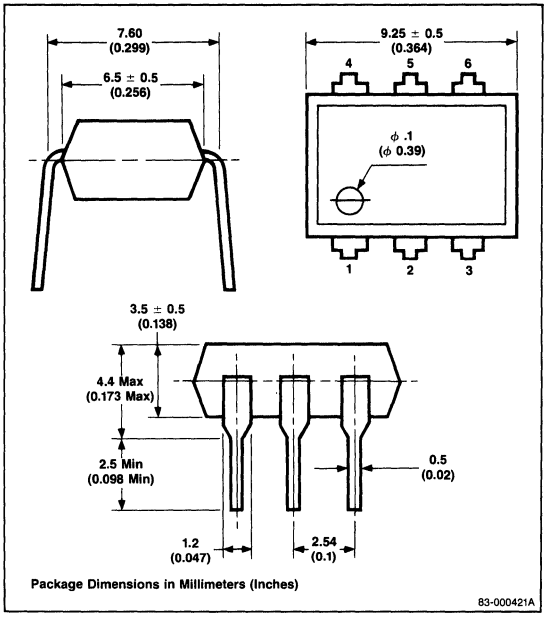
4N25
PHOTO COUPLER
SINGLE TRANSISTOR

NEPOC SERIES

Description

The 4N25 is an optically coupled isolator containing a GaAs light emitting diode and an NPN silicon photo transistor.

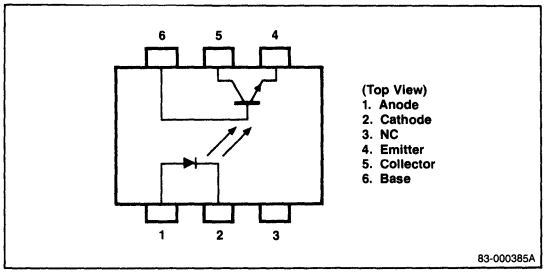
Package Dimensions



Package Dimensions in Millimeters (Inches)

83-000421A

Pin Connection



83-000385A

Features

- ☐ High isolation voltage: $2500V_{DC}$
- ☐ High transfer ratio: 20% min
- ☐ High speed switching: t_r, t_f = 4μs typ
- ☐ Economical, compact, dual in-line plastic package

Applications

- ☐ Interface circuit for various instruments and control equipment
- ☐ Chopper circuits
- ☐ Computer and peripheral manufacture
- ☐ Pulse transformers
- ☐ Data communication equipment

Absolute Maximum Ratings

T_A = +25°C

Diode	
Reverse Voltage, V_R	5.0V
Forward Current (DC), I_F	80mA
Power Dissipation, P_D	150mW
Peak Forward Current (300μs, 2% duty cycle), $I_{F(peak)}$	3A
Transistor	
Collector to Emitter Voltage, V_{CEO}	30V
Collector to Base Voltage, V_{CBO}	70V
Emitter to Collector Voltage, V_{ECO}	7V
Collector Current, I_C	100mA
Power Dissipation, P_D	150mW
Isolation Voltage[1], BV	$2500V_{DC}$
Isolation Voltage[1], BV	$2000V_{AC}$
Storage Temperature, T_{STG}	−55°C to +150°C
Operating Temperature, T_{OPT}	−55°C to +100°C
Lead Temperature (Soldering 10s)	260°C
Total Power Dissipation, P_T	250mW

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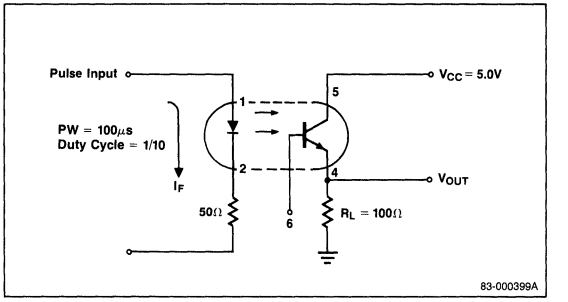
Electrical Characteristics
T_A = +25°C

Parameter	Symbol	Limits Min	Typ	Max	Unit	Test Conditions
Diode						
Forward Voltage	V_F		1.1	1.4	V	I_F = 10mA
Forward Voltage	V_F		1.2	1.5	V	I_F = 50mA
Reverse Current	I_R			10	μA	V_R = 5V
Junction Capacitance	C		50		pF	V = 0, f = 1.0MHz
Transistor						
Collector to Emitter Dark Current	I_{CEO}			50	nA	V_{CE} = 10V, I_F = 0
DC Current Gain	h_{FE}		500			I_C = 2mA, V_{CE} = 5.0V
Collector to Emitter Breakdown Voltage	BV_{CEO}	30	60		V	I_C = 1mA, I_B = 0
Collector to Base Breakdown Voltage	BV_{CBO}	70	120		V	I_C = 100μA, I_E = 0
Emitter to Collector Breakdown Voltage	BV_{ECO}	7	9		V	I_E = 100μA, I_B = 0
Coupled						
Current Transfer Ratio	CTR (I_C/I_F)	20			%	I_F = 10mA, V_{CE} = 5.0V
Collector Saturation Voltage	$V_{CE(sat)}$			0.3	V	I_F = 10mA, I_C =2.0mA
Isolation Resistance	R_{1-2}	10^{11}			Ω	V_{IN-OUT} = 1.0kV
Isolation Capacitance	C_{1-2}		0.8		pF	V = 0, f = 1.0MHz
Rise Time	t_r		4		μs	V_{CC} = 5.0V, I_C = 2mA, R_L = 100Ω[2]
Fall Time	t_f		4		μs	V_{CC} = 5.0V, I_C = 2mA, R_L = 100Ω[2]

Notes: 1. Measuring Conditions: DC or AC voltage for 1 min at T_A = +25°C, RH = 60% between input (pins 1, 2, and 3 common) and output (pins 4, 5, and 6 common).

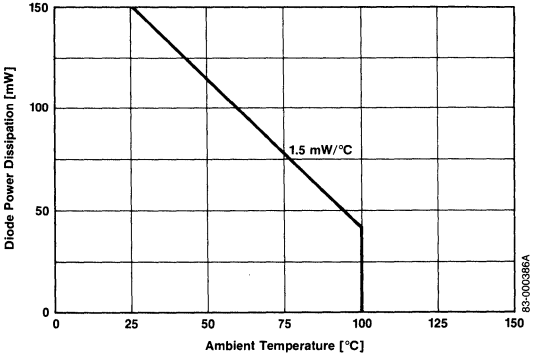
2. Test circuit for switching time.

Test circuit for switching time

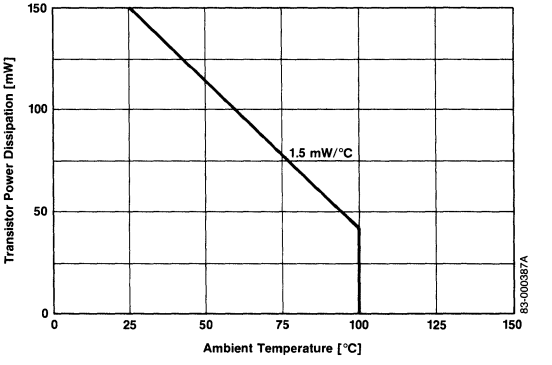


Typical Characteristics
T_A = +25°C

Diode Power Dissipation vs Ambient Temperature



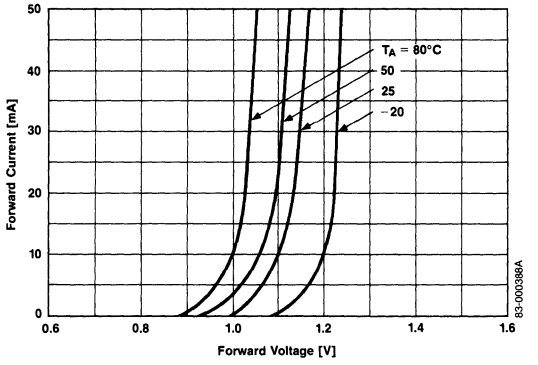
Transistor Power Dissipation vs Ambient Temperature



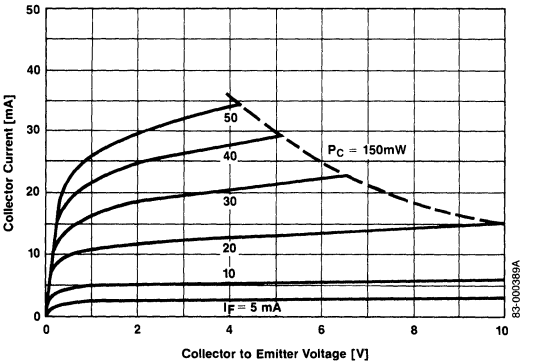
Typical Characteristics (cont)

T_A = +25°C

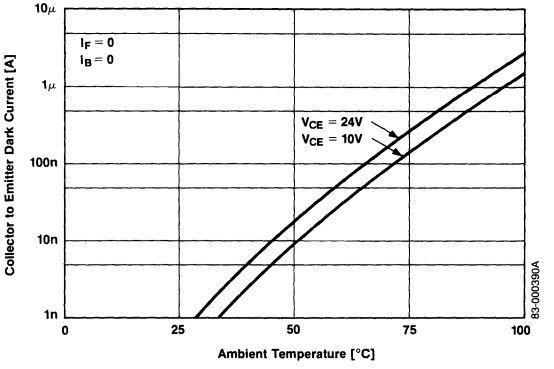
Forward Current vs Forward Voltage



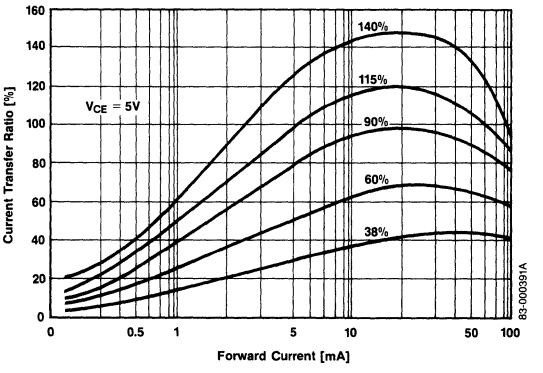
Collector Current vs Collector to Emitter Voltage



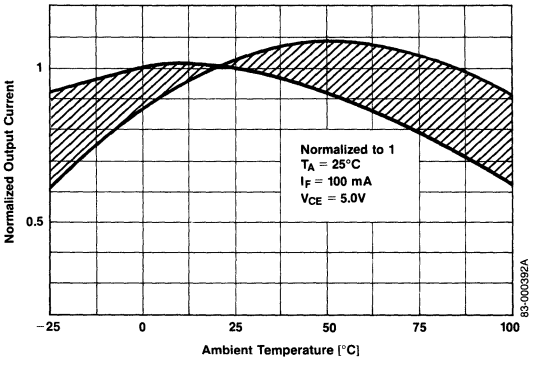
Collector to Emitter Dark Current vs Ambient Temperature



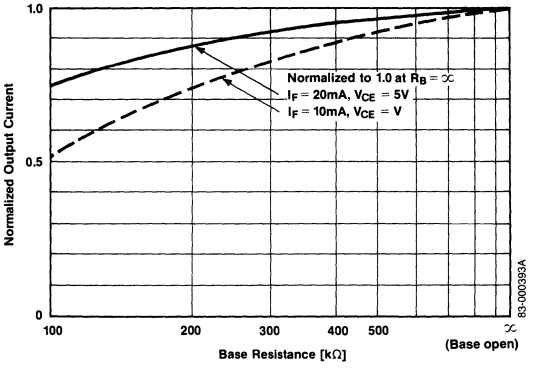
Current Transfer Ratio vs Forward Current



Normalized Output Current vs Ambient Temperature



Normalized Output Current vs Base Resistance



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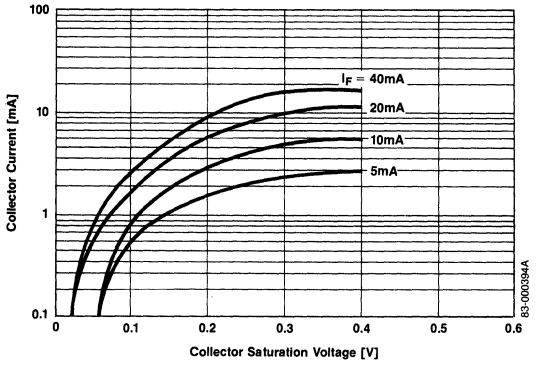
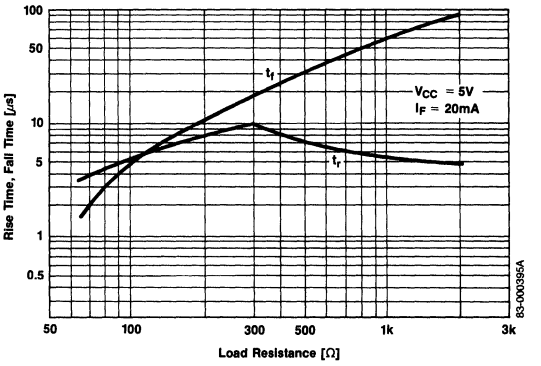
Typical Characteristics (cont)

T_A = +25°C

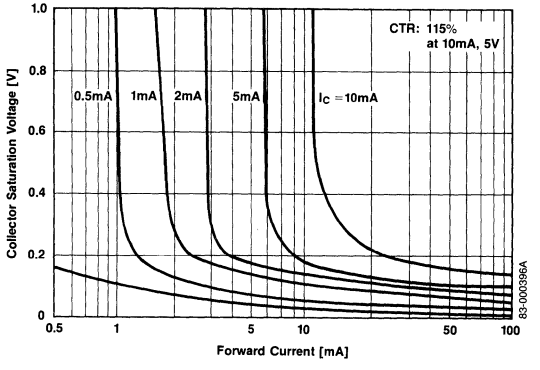
Collector Current vs Collector Saturation Voltage



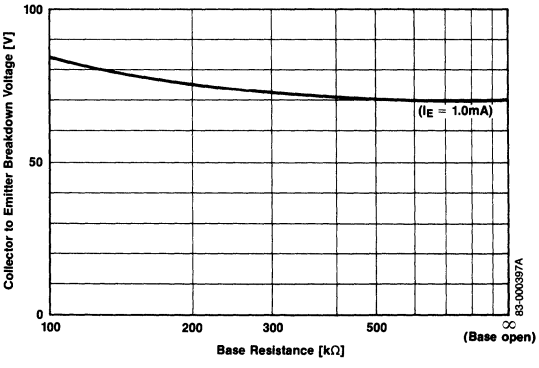
Switching Time vs Load Resistance



Saturation Voltage vs Forward Current



Collector to Emitter Breakdown Voltage vs Base Resistance



Frequency Response